

FORM PTO-1449 (MODIFIED) LIST OF PATENTS AND PUBLICATIONS FOR APPLICANTS INFORMATION DISCLOSURE STATEMENT	ATTORNEY DOCKET NO.	SERIAL NO.
	SP00-268	09/886,873
	APPLICANT Stellmacher et al. FILING DATE 06.21.01	
		GROUP: TBA 2874

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REFERENCE DESIGNATION				U.S. PATENT DOCUMENTS			
Examiner Initial		Document Number	Date	Name	Class	Sub-Class	Filing Date if Approp.
JD	AA	5.351.323	9/27/94	Miller. et al	385	28	
JD	AB	6.025.207	2/15/00	Mersali. et al	438	29	
JD	AC	5.703.895	12/30/97	Ghirardi. et al	372	50	
JD	AD	6.072.812	6/6/00	Eng	372	20	
JD	AE	4.688.062	8/18/87	Liles	357	22	
JD	AF	4.745.448	5/17/88	Van Rees, et al	357	22	
JD	AG	4.340.966	7/20/82	Akiba, et al	375	45	
	AH						
	AI						
	AJ						
	AK						

FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Sub-Class	Translation Yes No
	AL						
	AM						
	AN						
	AO						
	AP						
	AQ						

OTHER ART (Including Author. Title. Date. Pertinent Pages. etc.)		
JD	AR	Efficient fiber coupling to low-loss diluted multiple quantum well optical waveguides - Deri. et al. Appl. Phys. Lett. 55 (15) 10/9/89 1495-1497
JD	AS	Analysis. design and fabrication of tapered integrated optical structures Optics Research Group - Daoping Li PhD Theses
JD	AT	1.3 μ m Polarization Insensitive Amplifier with Integrated Mode Transformer - Tishinin. et al Department of Electrical Engineering/Electrophysics www-scf.edu.
JD	AU	Photonic Application Specified Integrated Circuits (PHASICs) for Photonic Networks - Hamacher. et al. Letzte Anderung: 9/98

Information Disclosure Statement-PTO-1449 (Modified)

Attachment to paper # 0204

JD	AV	Optoelectronics Packaging: An Enabling Technology – M. Dagenais www.ieee.org/organiations/pubs/newsletters/leos/apr97/html/feature.htm
JD	AW	Alignment Tolerant Lasers and Silicon Waferboard Integration – Dagenais. et al. Dept. of EE and Laboratory for Physical Sciences U. of MD. Collage Park. MD
JD	AX	Carrier-induced change due to doping in refractive index of InP: Measurements at 1.3 and 1.5 μ m – L. Chusseau. et al – Appl. Phys. Lett. 69 (20) 11/11/96
JD	AY	INGaAsP/InP tapered active layer multiquantum well laser with 1.8dB coupling loss to cleaved singledmode fibre.- Lealman et al – Electronics Letters 9/29/94 Vol. 30 No. 20 pages 1685-1687
JD	AZ	Low-loss beamwidth transformers on InP with reduced requirements on lithographic resolution.- R. Zengerle J. Vac. Sci. Technol. B. Vol. 11. No. 6. Nov/Dec 93 page 2641 - 2644
JD	BA	Low-Loss Fibre-Chip Coupling by Buried Laterally Tapered Inp/InGaAsp Waveguide Structure – R. Zengerle, et al Electronics Letters 3/26/92 Vol. 28 No. 7

EXAMINER:

Jennifer Doan

DATE CONSIDERED:

01/30/04

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609: draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.